

2SC4404

T-31-15

2059

NPN Epitaxial Planar Silicon Transistor

**UHF Local OSC, Wide-Band
Amp Applications**

©2757

Applications

- UHF OSC, wide-band amplifiers

Features

- High cutoff frequency : $f_T = 5.0\text{GHz}$ typ
- High power gain : $\text{MAG} = 14\text{dB}$ typ ($f = 0.9\text{GHz}$)
- Small noise figure : $\text{NF} = 2.2\text{dB}$ typ ($f = 0.9\text{GHz}$)
- Very small-sized package permitting 2SC4404-applied sets to be made smaller and slimmer

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

			unit
Collector to Base Voltage	V_{CB0}	20	V
Collector to Emitter Voltage	V_{CE0}	12	V
Emitter to Base Voltage	V_{EB0}	3	V
Collector Current	I_C	70	mA
Collector Dissipation	P_C	150	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics at $T_a = 25^\circ\text{C}$

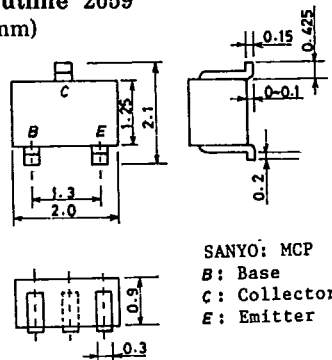
			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 12\text{V}, I_E = 0$			1.0	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 2\text{V}, I_C = 0$			10	μA
DC Current Gain	h_{FE}	$V_{CE} = 10\text{V}, I_C = 20\text{mA}$	≈ 40		≈ 200	
Gain-Bandwidth Product	f_T	$V_{CE} = 10\text{V}, I_C = 20\text{mA}$		5.0		GHz
Output Capacitance	c_{ob}	$V_{CB} = 10\text{V}, f = 1\text{MHz}$		0.75	1.1	pF
Reverse Transfer Capacitance	c_{re}	$V_{CB} = 10\text{V}, f = 1\text{MHz}$		0.5		pF
Forward Transfer Gain	$ S_{21} ^2$	$V_{CE} = 10\text{V}, I_C = 20\text{mA}, f = 0.9\text{GHz}$		14		dB
Maximum Available Power Gain	MAG	$V_{CE} = 10\text{V}, I_C = 20\text{mA}, f = 0.9\text{GHz}$		14		dB
Noise Figure	NF	$V_{CE} = 10\text{V}, I_C = 5\text{mA}, f = 0.9\text{GHz}$		2.2		dB

See specified Test Circuit.

※ The 2SC4404 is classified by 20mA h_{FE} as follows:

40	2	80	60	3	120	100	4	200
----	---	----	----	---	-----	-----	---	-----

- (Note) Marking : NY
 h_{FE} rank : 2, 3, 4
 ● For CP package version, use the 2SC3774.

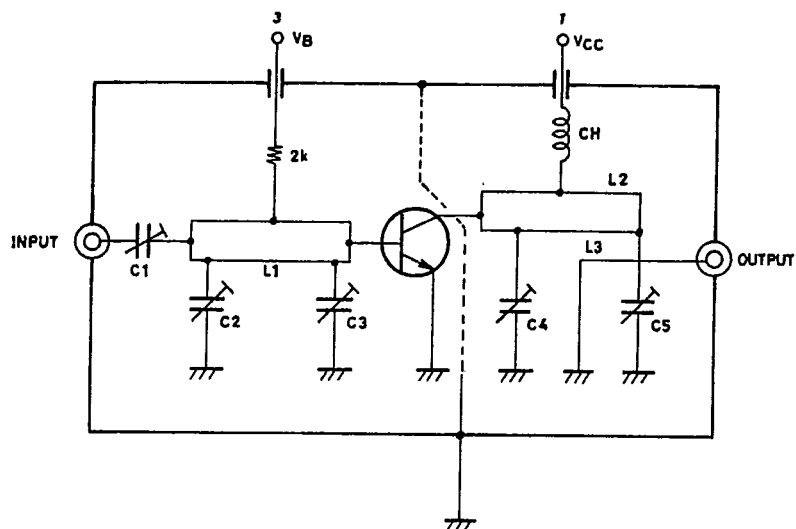
Case Outline 2059
(unit : mm)

4298TA, TS No. 2757-1/4

2SC4404

T-31-15

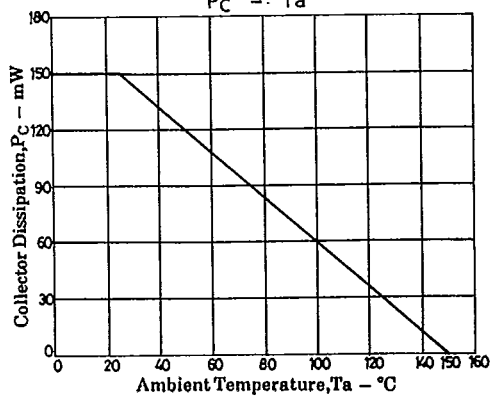
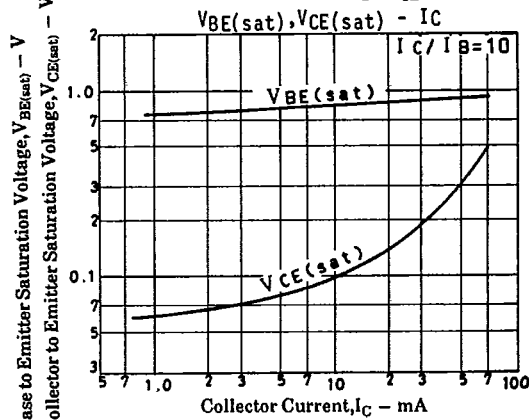
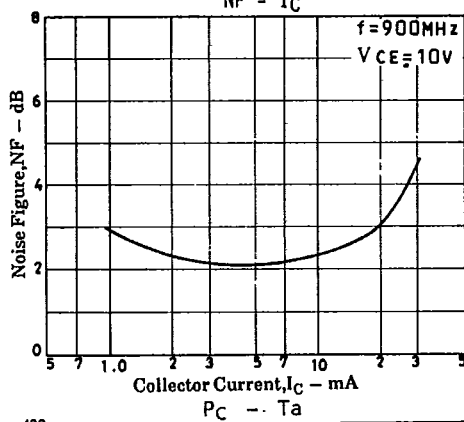
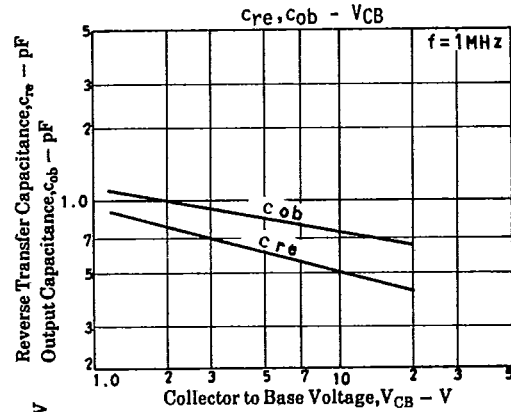
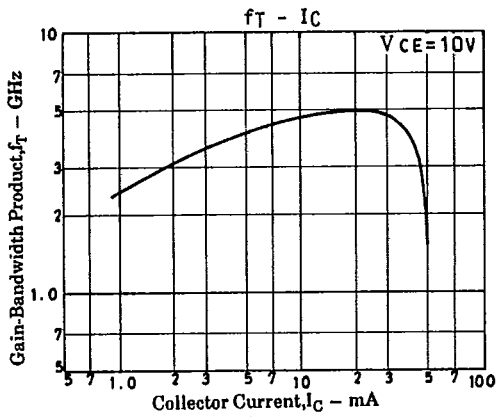
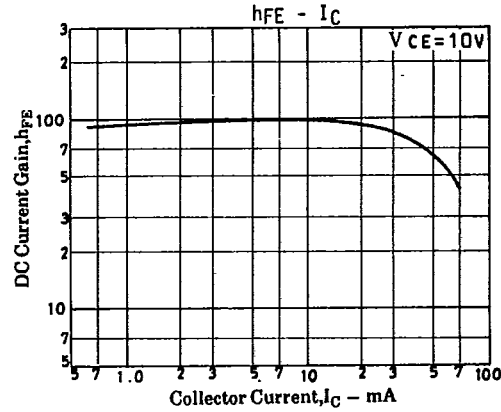
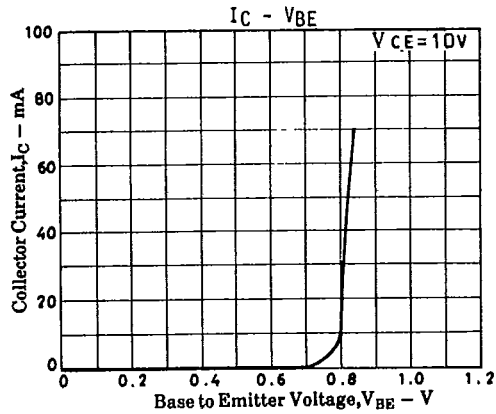
NF Test Circuit



	900MHz
C 1	$\sim 5 \text{ pF}$
C 2	$\sim 10 \text{ pF}$
C 3	$\sim 10 \text{ pF}$
C 4	$\sim 10 \text{ pF}$
C 5	$\sim 10 \text{ pF}$
L 1	$W \div 1.5 \text{ mm}, l \div 2.5 \text{ mm}$ strip line
L 2	$W \div 4 \text{ mm}, l \div 2.5 \text{ mm}$ strip line
L 3	$0.5 \phi, l \div 4.0 \text{ mm}$
CH	$2t + \text{bead core}$

2SC4404

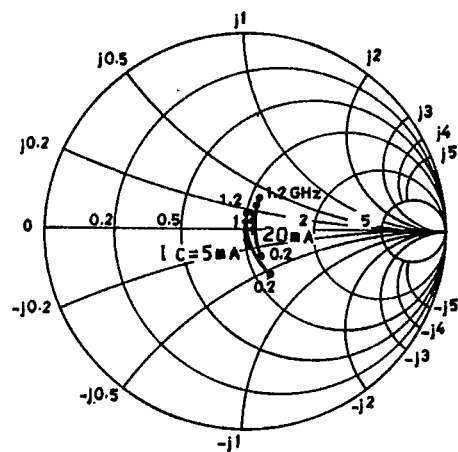
T-31-15



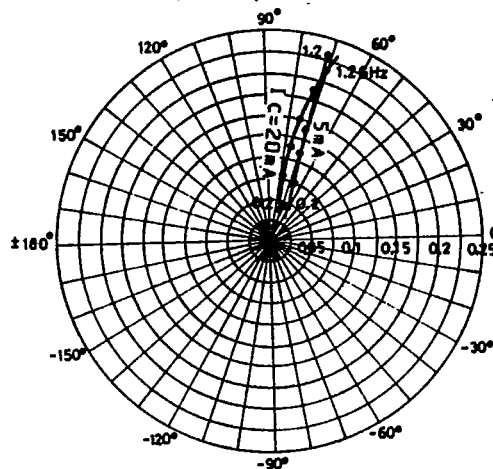
2SC4404

T-31-15

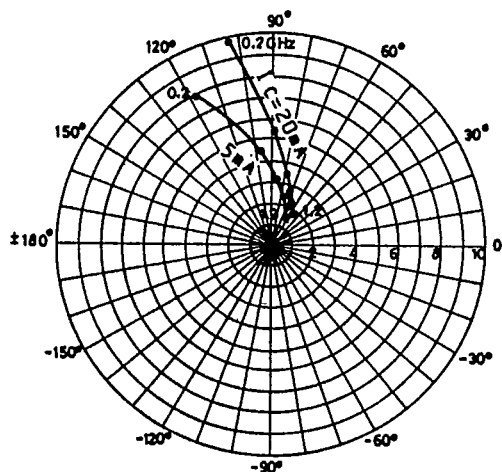
S11e : VCE=10V
f=200MHz step



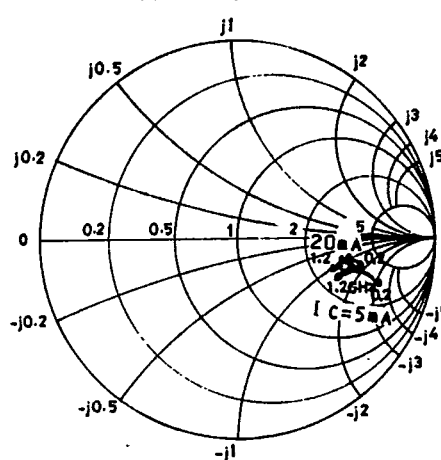
S12e : VCE=10V
f=200MHz step



S21e : VCE=10V
f=200MHz step



S22e : VCE=10V
f=200MHz step

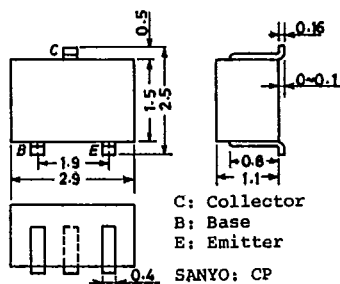


T-91-20

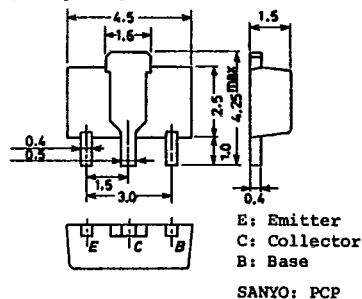
CASE OUTLINES OF SURFACE MOUNT TRANSISTORS

- All of Sanyo surface mount transistor case outlines are illustrated below.
- All dimensions are in mm, and dimensions which are not followed by min. or max. are represented by typical values.
- No marking is indicated.

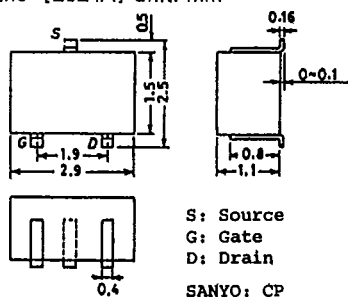
Case Outline—[2018A] unit: mm



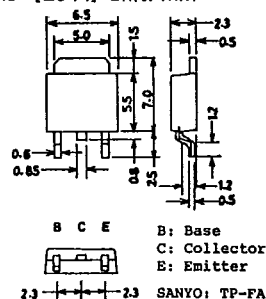
Case Outline—[2038] unit: mm



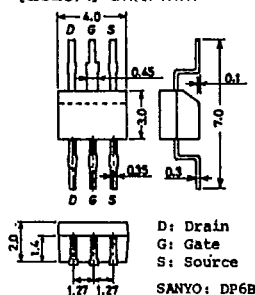
Case Outline—[2024A] unit: mm



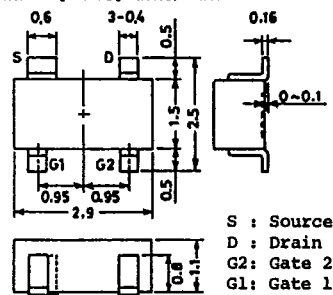
Case Outline—[2044] unit: mm



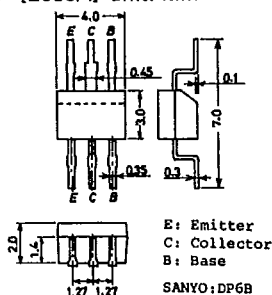
Case Outline—[2028A] unit: mm



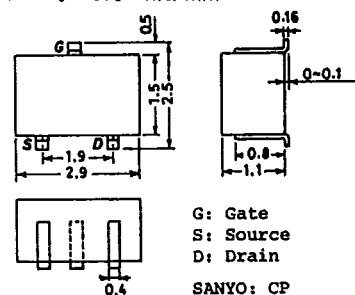
Case Outline—[2046] unit: mm



Case Outline—[2030A] unit: mm

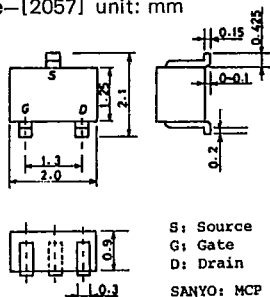


Case Outline—[2050] unit: mm

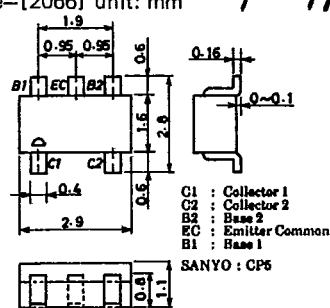


T-91-20

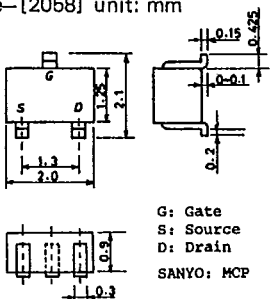
Case Outline—[2057] unit: mm



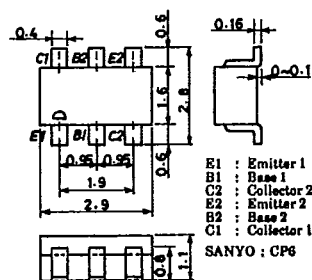
Case Outline—[2066] unit: mm



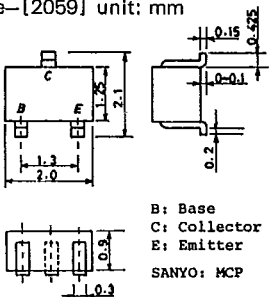
Case Outline—[2058] unit: mm



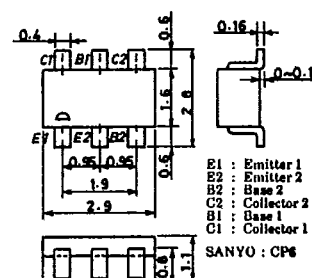
Case Outline—[2067] unit: mm



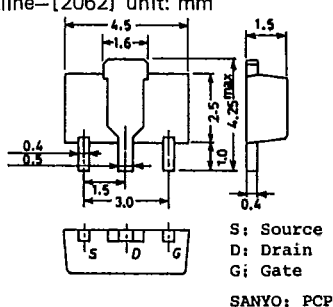
Case Outline—[2059] unit: mm



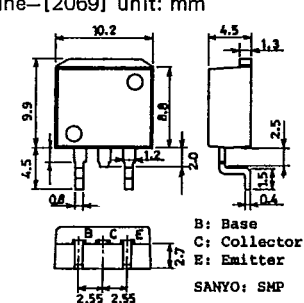
Case Outline—[2068] unit: mm



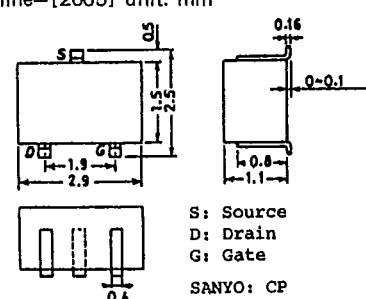
Case Outline—[2062] unit: mm



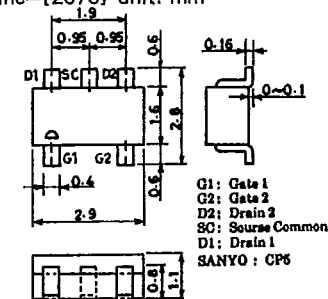
Case Outline—[2069] unit: mm



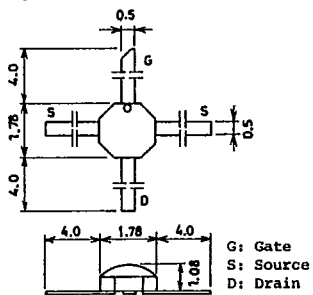
Case Outline—[2065] unit: mm



Case Outline—[2070] unit: mm

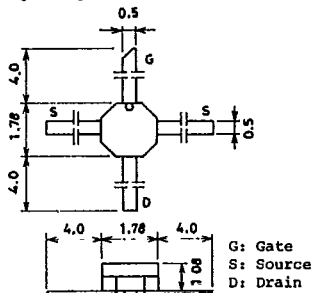


Case Outline—[2071] unit: mm



T-9120

Case Outline—[2072] unit: mm



Case Outline—[2073] unit: mm

